(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
28 April 2011 (28.04.2011)

PCT

(10) International Publication Number
WO 2011/049620 A3

(51) International Patent Classification:
H01L 21/68 (2006.01)

(21) International Application Number:
PCT/US2010/002794

(22) International Filing Date:
20 October 2010 (20.10.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/582,991 21 October 2009 (21.10.2009) US

(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538-6470 (US).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **SINGH, Harmeet** [US/US]; 759 Praderia Circle, Fremont, CA 94539 (US). **GAFF, Keith** [AU/US]; 5363 Granville Court, Fremont, CA 94536 (US). **BENJAMIN, Neil** [GB/US]; 216 Green Street, East Palo Alto, CA 94303 (US). **COMENDANT, Keith** [US/US]; 4350 Glidden Way, Fremont, CA 94536 (US).

(74) Agent: **SKIFF, Peter, K.**; Buchanan Ingersoll & Rooney P.C., (Customer No. 21839), P. O. Box 1404, Alexandria, VA 22313-1404 (US).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

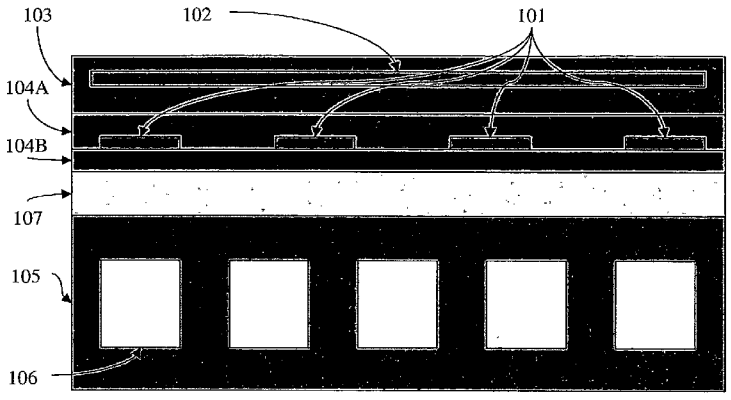
Published:

— *with international search report (Art. 21(3))*

(88) Date of publication of the international search report:
3 November 2011

(54) Title: HEATING PLATE WITH PLANAR HEATER ZONES FOR SEMICONDUCTOR PROCESSING

Fig.1



(57) Abstract: A heating plate for a substrate support assembly in a semiconductor plasma processing apparatus, comprises multiple independently controllable planar heater zones arranged in a scalable multiplexing layout, and electronics to independently control and power the planar heater zones. A substrate support assembly in which the heating plate is incorporated includes an electrostatic clamping electrode and a temperature controlled base plate. Methods for manufacturing the heating plate include bonding together ceramic or polymer sheets having planar heater zones, power supply lines, power return lines and vias.

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